

Sheet 1 of 1

**INFORMATION DISCLOSURE  
CITATION**

ATTY. DOCKET NO.

160-410

**APPLICANT**

NAKAMURA et al

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March 16, 2004

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TC/A.U.

2814

(Use several sheets if necessary)

**U.S. PATENT DOCUMENTS**

[illegible]

FOREIGN PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS							
DOCUMENT	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION		
					YES	NO	
TD	JP 9-64419	03/1997	JAPAN			x	
TD	JP 8-293643	11/1996	JAPAN			x	
TD	JP 7-249795	09/1995	JAPAN			x	

OTHER DOCUMENTS (including Author, Title, Date, Pertinent pages, etc.)  
 220 54410 (03/1997) together w/Abstract (12 pgs.)

OTHER DOCUMENTS (including Author, Title, Date, Pertinent Pgs.)	
TD	Computer English Translation of JP 9-64419 (03/1997) together w/Abstract (12 pgs.)
TD	Computer English Translation of JP 8-293643 (11/1996) together w/Abstract (15 pgs.)
TD	Computer English Translation of JP 7-249795 (09/1995) together w/Abstract (14 pgs.)
TD	KUGA et al., "Violet and Near-UV Light Emission from GaN/Al <sub>0.08</sub> Ga <sub>0.92</sub> N Injection Diode Grown on (0001) 6H-SiC Substrate by Low-Pressure Metal-Organic Vapor Phase Epitaxy," Jpn. J. Appl. Phys., Vol. 34, Part 1, No. 8A (1995), pp. 4085-4086

\*Examiner

/Theresa Doan/

Date Considered \_\_\_\_\_

08/29/2006

*Examiner	/Theresa Doan/	Date Considered	
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Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to application.

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